

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Ken YOSHIZAWA

Application No.: New U.S. National Stage of
PCT/JP2004/009921

Filed: January 19, 2006

Docket No.: 126623

For: A METHOD FOR PRODUCING A SILICON WAFER AND A SILICON WAFER

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 CFR §1.56, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO-1449. Unless otherwise indicated herein, one copy of each reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

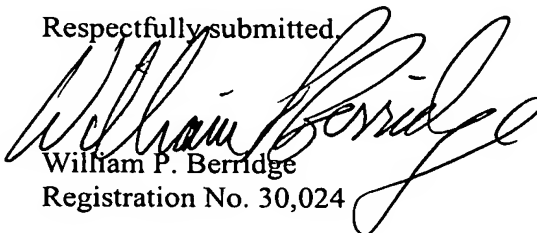
- ☒ 1. This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date of this non-CPA application, OR (b) before the mailing date of a first Office Action on the merits in the present application. No certification or fee is required.
- ☒ 2. Relevance of the non-English language reference 1 is discussed in the present specification.
- ☒ 3. The references 2-3 were cited in a counterpart foreign application. An English language version of the foreign search report is attached for the Examiner's information.
- ☒ 4. English language Abstracts of the non-English language references 1-3 are attached hereto.

IAP20 REG 10 JAN 2006



5. A computer-generated English language translation of the following Japanese Patent Publication has been obtained from the website of the Japanese Patent Office ([<http://www.jpo.go.jp>]), and is attached, but has not been reviewed for accuracy. See References 1-2.

Respectfully submitted,


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Date: January 19, 2006

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Sheet 1 of 1

Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 126623		APPLICATION NO. New U.S. National Stage of PCT/JP2004/009921 10/583108	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANTS Ken YOSHIZAWA			
				FILING DATE January 19, 2006		GROUP	

U.S. PATENT DOCUMENTS						
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS

FOREIGN PATENT DOCUMENTS						
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS
	1	JP A 09-165298 w/ abst & transl	6/24/1997	JAPAN		
	2	JP A 2002-025874 w/ abst & transl	1/25/2002	JAPAN		
	3	JP A 04-002683 w/ abst	1/7/1992	JAPAN		

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)		
4		DYER, "Dislocation-Free Czochralski Growth of <110> Silicon Crystals," Journal of Crystal Growth, vol. 47, pp. 533-540 {1979}
5		MURTHY, "Growth of Dislocation-Free Silicon Crystals in the <110> Direction for Use as Neutron Monochromators," Journal of Crystal Growth, vol. 52, pp. 391-395 {1981}

EXAMINER	DATE CONSIDERED
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

Date: January 19, 2006